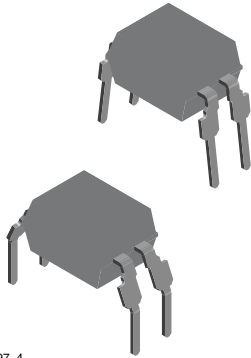
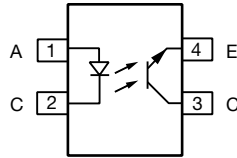


Optocoupler, Phototransistor Output



17197_4



17918_14

DESCRIPTION

The TCET1200 consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 4 pin plastic dual inline package.

VDE STANDARDS

These couplers perform safety functions according to the following equipment standards:

- **DIN EN 60747-5-2 (VDE 0884)**
Optocoupler for electrical safety requirements
- **IEC 60950/EN 60950**
Office machines (applied for reinforced isolation for mains voltage $\leq 400 V_{RMS}$)
- **VDE 0804**
Telecommunication apparatus and data processing
- **IEC 60065**
Safety for mains-operated electronic and related household apparatus

FEATURES

- High common mode rejection
- CTR offered in 5 groups
- Low temperature coefficient of CTR
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC



RoHS
COMPLIANT

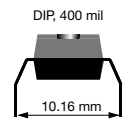
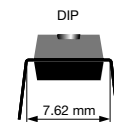
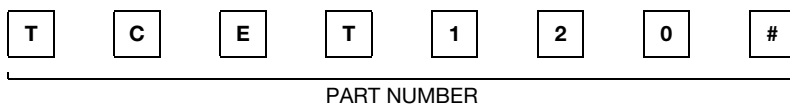
APPLICATIONS

- Switch-mode power supplies
- Line receiver
- Computer peripheral interface
- Microprocessor system interface
- Reinforced isolation provides circuit protection against electrical shock (safety class II)
- Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):
 - for appl. class I - IV at mains voltage $\leq 300 V$
 - for appl. class I - III at mains voltage $\leq 600 V$ according to DIN EN 60747-5-2 (VDE 0884)

AGENCY APPROVALS

- UL1577, file no. E52744, double protection
- cUL tested to CSA 22.2 bulletin 5A, double protection
- BSI IEC 60950; IEC 60065 pending
- DIN EN 60747-5-2 (VDE 0884)
DIN EN 60747-5-5 (pending)
- FIMKO

ORDERING INFORMATION



AGENCY CERTIFIED/PACKAGE	CTR (%)				
	5 mA	10 mA			
UL, VDE, BSI, FIMKO	50 to 600	40 to 80	63 to 125	100 to 200	160 to 320
DIP-4	TCET1200	TCET1201	TCET1202	TCET1203	TCET1204
DIP-4, 400 mil	TCET1200G	TCET1201G	TCET1202G	TCET1203G	TCET1204G

Note

- G = leadform 10.16 mm; G is not marked on the body.

ABSOLUTE MAXIMUM RATINGS (1) ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V_R	6	V
Forward current		I_F	60	mA
Forward surge current	$t_p \leq 10\text{ }\mu\text{s}$	I_{FSM}	1.5	A
Power dissipation		P_{diss}	70	mW
Junction temperature		T_j	125	$^{\circ}\text{C}$
OUTPUT				
Collector emitter voltage		V_{CEO}	70	V
Emitter collector voltage		V_{ECO}	7	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10\text{ ms}$	I_{CM}	100	mA
Power dissipation		P_{diss}	70	mW
Junction temperature		T_j	125	$^{\circ}\text{C}$
COUPLER				
Isolation test voltage (RMS)		V_{ISO}	5000	V_{RMS}
Total power dissipation		P_{tot}	200	mW
Operating ambient temperature range		T_{amb}	- 40 to + 100	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 55 to + 125	$^{\circ}\text{C}$
Soldering temperature (2)	2 mm from case, $t \leq 10\text{ s}$	T_{sld}	260	$^{\circ}\text{C}$

Notes

(1) Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

(2) Refer to wave profile for soldering conditions for through hole devices.

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						
Forward voltage	$I_F = 50\text{ mA}$	V_F		1.25	1.6	V
Junction capacitance	$V_R = 0\text{ V}, f = 1\text{ MHz}$	C_j		50		pF
OUTPUT						
Collector emitter voltage	$I_C = 1\text{ mA}$	V_{CEO}	70			V
Emitter collector voltage	$I_E = 100\text{ }\mu\text{A}$	V_{ECO}	7			V
Collector emitter cut-off current	$V_{CE} = 20\text{ V}, I_F = 0\text{ A}, E = 0$	I_{CEO}		10	100	nA
COUPLER						
Collector emitter saturation voltage	$I_F = 10\text{ mA}, I_C = 1\text{ mA}$	V_{CEsat}			0.3	V
Cut-off frequency	$V_{CE} = 5\text{ V}, I_F = 10\text{ mA}, R_L = 100\text{ }\Omega$	f_c		110		kHz
Coupling capacitance	$f = 1\text{ MHz}$	C_k		0.6		pF

Note

- Minimum and maximum values were tested requirements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
I_C/I_F	$V_{CE} = 5\text{ V}, I_F = 5\text{ mA}$	TCET1200	CTR	50		600	%
		TCET1200G	CTR				%
	$V_{CE} = 5\text{ V}, I_F = 10\text{ mA}$	TCET1201	CTR	40		80	%
			TCET1201G				CTR
		TCET1202	CTR	63		125	%
			TCET1202G				CTR
		TCET1203	CTR	100		200	%
			TCET1203G				CTR
		TCET1204	CTR	160		320	%
			TCET1204G				CTR

SAFETY AND INSULATION RATED PARAMETERS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Partial discharge test voltage - routine test	100 %, $t_{\text{test}} = 1\text{ s}$	V_{pd}	1.6			kV
Partial discharge test voltage - lot test (sample test)	$t_{\text{Tr}} = 60\text{ s}, t_{\text{test}} = 10\text{ s}$, (see figure 2)	V_{pd}	1.36			kV
Insulation resistance	$V_{\text{IO}} = 500\text{ V}$	R_{IO}	10^{12}			Ω
	$V_{\text{IO}} = 500\text{ V}, T_{\text{amb}} = 100\text{ }^\circ\text{C}$	R_{IO}	10^{11}			Ω
	$V_{\text{IO}} = 500\text{ V}, T_{\text{amb}} = 150\text{ }^\circ\text{C}$ (construction test only)	R_{IO}	10^9			Ω
Rated impulse voltage		V_{IOTM}			6	kV
Max. working voltages	Recurring peak voltage	V_{IORM}	850			V
Forward current		I_F			130	mA
Power dissipation		P_{diss}			265	mW
Safety temperature		T_{si}			150	$^\circ\text{C}$
Creepage distance					7.6	mm

Note

- According to DIN EN 60747-5-2 (VDE 0884) (see figure 2). This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

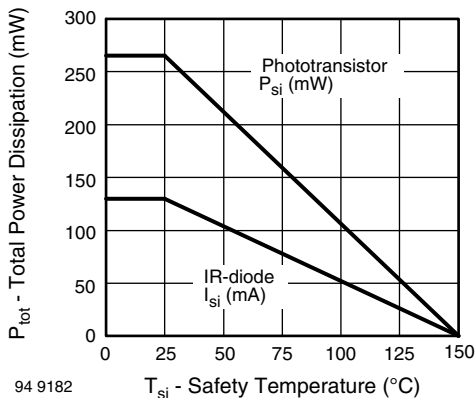


Fig. 1 - Derating Diagram

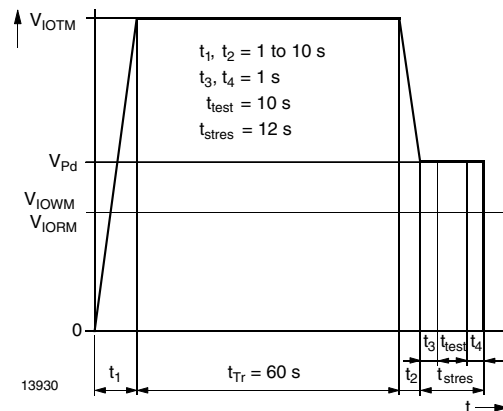


Fig. 2 - Test Pulse Diagram for Sample Test acc. to DIN EN 60747-5-2; IEC60747-5-5

SWITCHING CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Delay time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_d		3		μs
Rise time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_r		3		μs
Fall time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_f		4.7		μs
Storage time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_s		0.3		μs
Turn-on time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_{on}		6		μs
Turn-off time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_{off}		5		μs
Turn-on time	$V_S = 5\text{ V}$, $I_F = 10\text{ mA}$, $R_L = 1\text{ k}\Omega$, (see figure 4)	t_{on}		9		μs
Turn-off time	$V_S = 5\text{ V}$, $I_F = 10\text{ mA}$, $R_L = 1\text{ k}\Omega$, (see figure 4)	t_{off}		10		μs

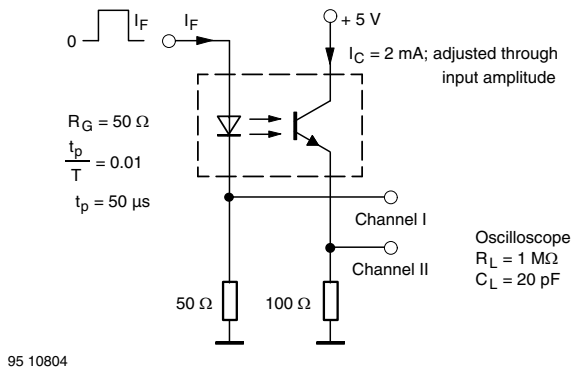


Fig. 3 - Test Circuit, Non-Saturated Operation

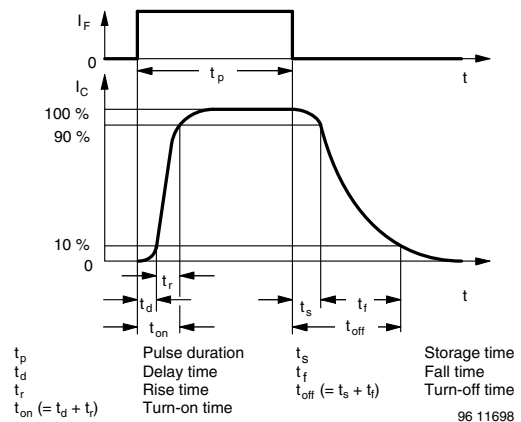


Fig. 5 - Switching Times

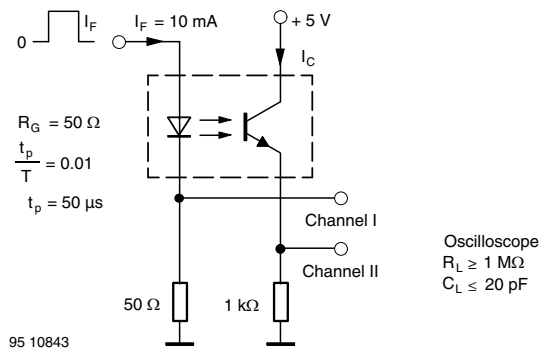


Fig. 4 - Test Circuit, Saturated Operation

TYPICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

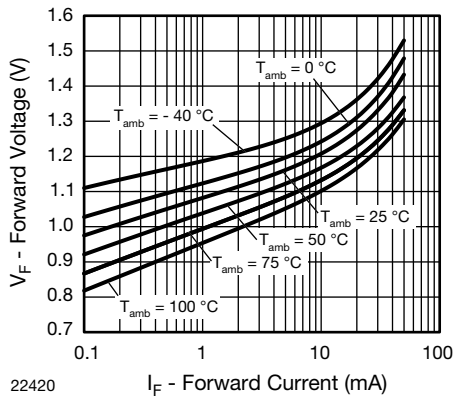


Fig. 6 - Forward Voltage vs. Forward Current

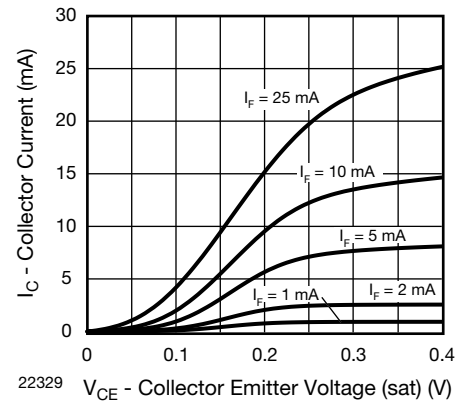


Fig. 9 - Collector Current vs. Collector Emitter Voltage (sat)

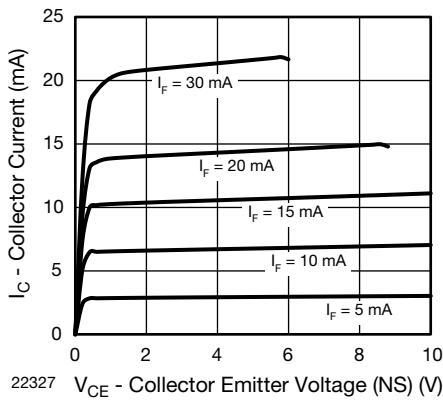


Fig. 7 - Collector Current vs. Collector Emitter Voltage (NS)

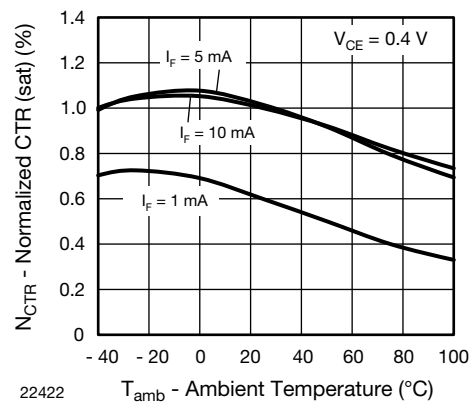


Fig. 10 - Normalized CTR (sat) vs. Ambient Temperature

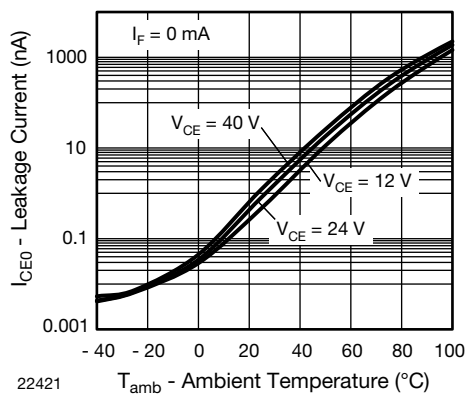


Fig. 8 - Leakage Current vs. Ambient Temperature

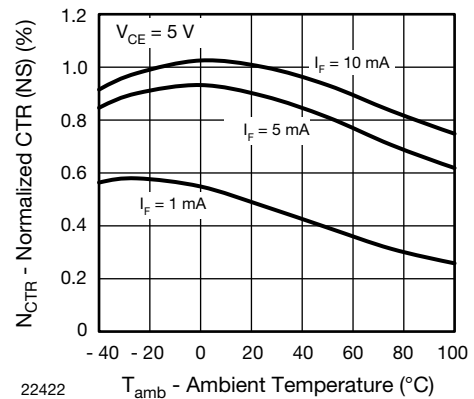


Fig. 11 - Normalized CTR (NS) vs. Ambient Temperature

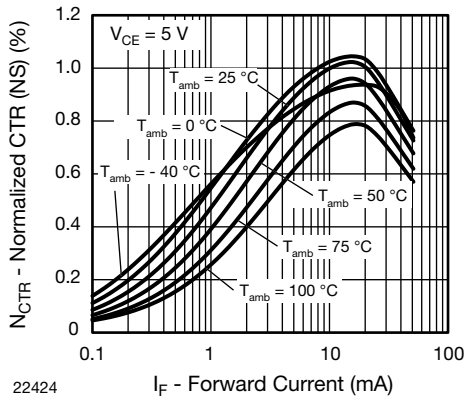


Fig. 12 - Normalized CTR (NS) vs. Forward Current

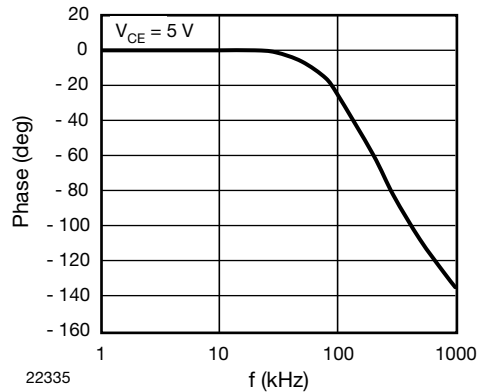


Fig. 15 - F_{CTR} vs. Phase Angle (kHz)

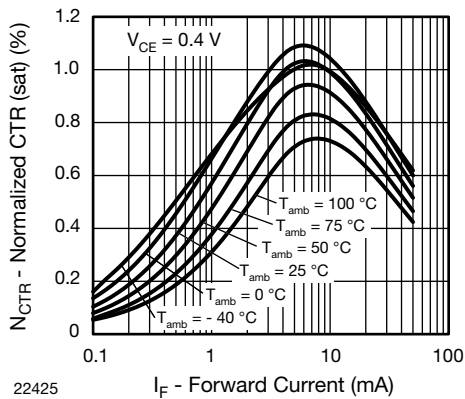


Fig. 13 - Normalized CTR (sat) vs. Forward Current

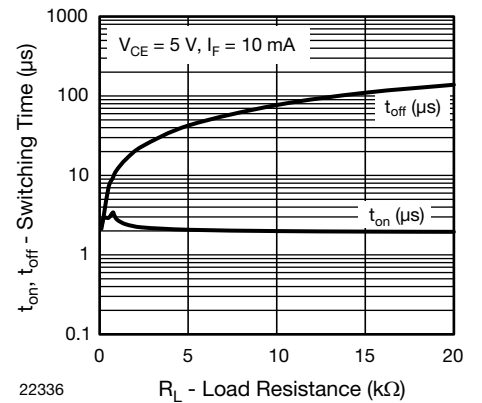


Fig. 16 - Switching Time vs. Load Resistance

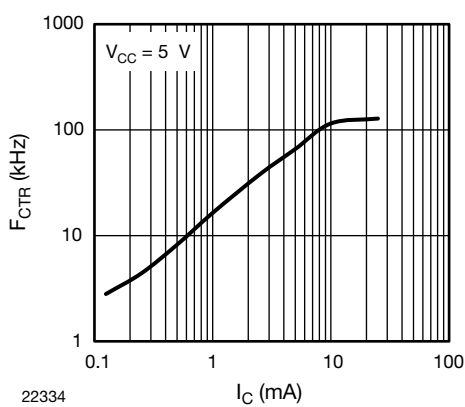


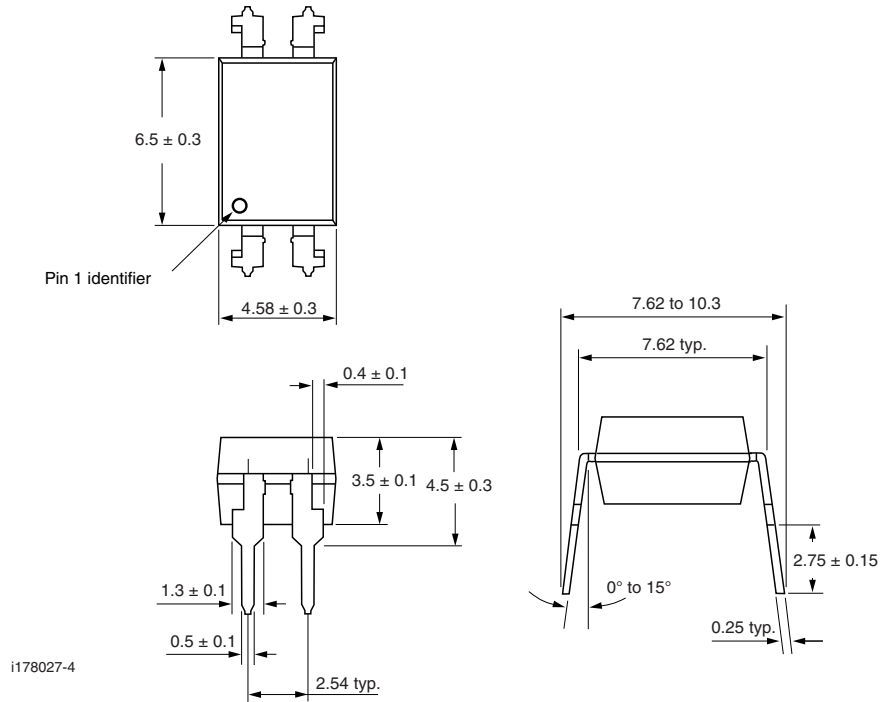
Fig. 14 - F_{CTR} vs. I_C (sat) (mA)



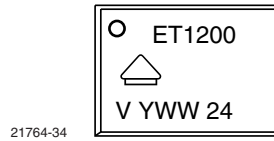
TCET1200, TCET1200G

Optocoupler, Phototransistor Output Vishay Semiconductors

PACKAGE DIMENSIONS in millimeters



PACKAGE MARKING



Note

- VDE logo is only printed on option 1 parts. Option information is not marked on the part.



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